

STD127DT4

High voltage fast-switching NPN power transistor

Datasheet - production data

Features

- NPN transistor
- High voltage capability
- Low spread of dynamic parameters
- Minimum lot-to-lot spread for reliable operation
- Very high switching speed
- Integrated anti-parallel collector emitter diode

Applications

- · Electronic ballast for fluorescent lighting
- Fly back and forward single transistor low power converters

Description

This device is manufactured using high voltage multi epitaxial planar technology for high switching speeds and medium voltage capability. It uses a cellular emitter structure with planar edge termination to enhance switching speeds while maintaining the wide RBSOA. The device is designed for use in lighting applications and low cost switch-mode power supplies.

Part number	Marking	Package	Packaging
STD127DT4	D127D	DPAK	Tape and reel

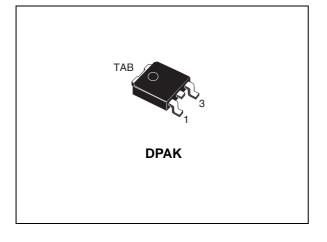
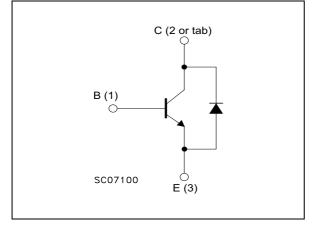


Figure 1. Internal schematic diagram



This is information on a product in full production.

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1 Electrical ratings

Symbol	Parameter	Value	Unit
V _{CES}	Collector-emitter voltage (V _{BE} = 0)	700	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	400	V
V _{EBO}	Emitter-base voltage ($I_C = 0$; $I_B = 2 \text{ A}$, $t_p < 10 \ \mu$ s, $T_J = 150 \ ^\circ\text{C}$)	V _{(BR)EBO}	V
۱ _C	Collector current	4	A
I _{CM}	Collector peak current (t _P < 5 ms)	8	A
I _B	Base current	2	A
I _{BM}	Base peak current (t _P < 5 ms)	4	А
P _{tot}	Total dissipation at $T_c \le 25 \text{ °C}$	35	W
T _{stg}	Storage temperature	-65 to 150	°C
TJ	Max. operating junction temperature	150	°C

Table	2.	Absolute	maximum	ratings
	~ .	Absolute	maximum	raungs

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thJC}	Thermal resistance junction-case max	3.57	°C/W
R _{thJA}	R _{thJA} Thermal resistance junction-ambient max		°C/W



2 Electrical characteristics

 $(T_{case} = 25^{\circ}C \text{ unless otherwise specified})$

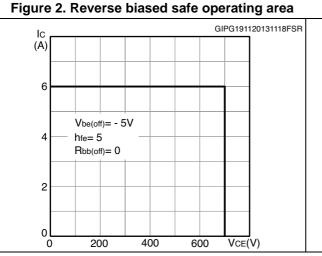
Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (V _{BE} =0)	V _{CE} = 700 V				100	μA
I _{CEO}	Collector cut-off current (I _B =0)	V _{CE} = 400 V				250	μA
V _{(BR)EBO}	Emitter - base breakdown voltage (I _C = 0)	I _E =10 mA		9		18	v
V _{CEO(sus)} ⁽¹⁾	Collector-emitter sustaining voltage $(I_B = 0)$	l _C =100 mA		400			v
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	I _C = 1 A I _C = 4 A	I _B = 0.2 A I _B = 1 A			0.3 1.3	V V
V _{BE(sat)} ⁽¹⁾	Base-emitter saturation voltage	l _C = 1 A	I _B = 0.2 A			1.2	v
		l _C = 10 mA	$V_{CE} = 5 V$	7			
h _{FE} ⁽¹⁾	DC current gain	I _C = 1 A		10	25	40	
		I _C = 4 A	V _{CE} = 5 V	5			
V _F	Diode forward voltage	I _F = 2 A				2.5	V
	Inductive load	I _C = 2 A	I _{B(on)} = 0.4 A				
t _s	Storage time	$V_{BE(off)} = -5 V;$			0.6		μs
t _f	Fall time	$V_{CC} = 200 V$	· · /		0.1		ns

Table 4	Electrical	characteristics
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1. Pulsed duration = 300 μ s, duty cycle \leq 1.5%.



2.1 Electrical characteristics (curves)





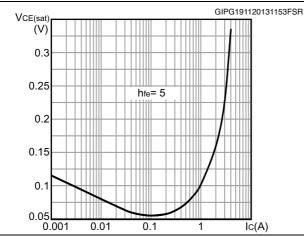
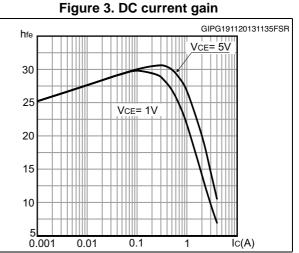


Figure 6. Base-emitter on-voltage





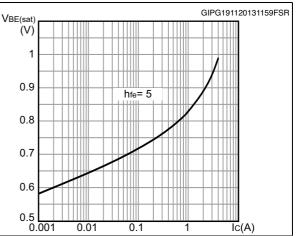
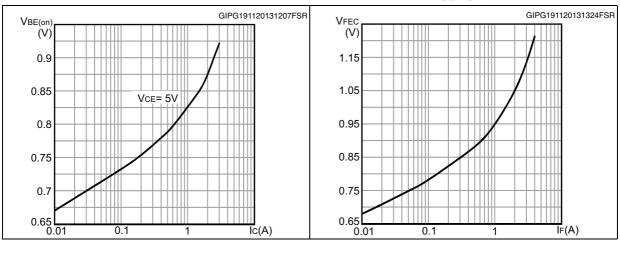


Figure 7. Diode forward voltage vs collector current





tstorage

t (ns)

1000

tr

td

1

100 _{tf}

10 0.5

Figure 8. Resistive load switching time

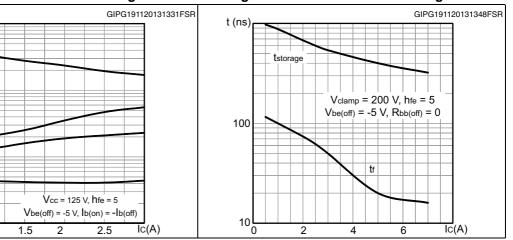
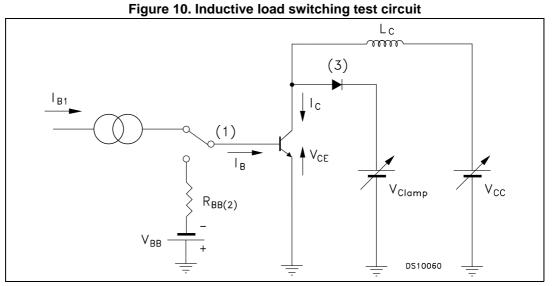


Figure 9. Inductive load switching time

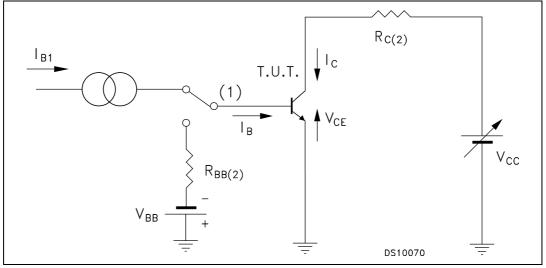


3 Test circuits



- 1. Fast electronic switch
- 2. Non-inductive resistor
- 3. Fast recovery rectifier

Figure 11. Resistive load switching test circuit





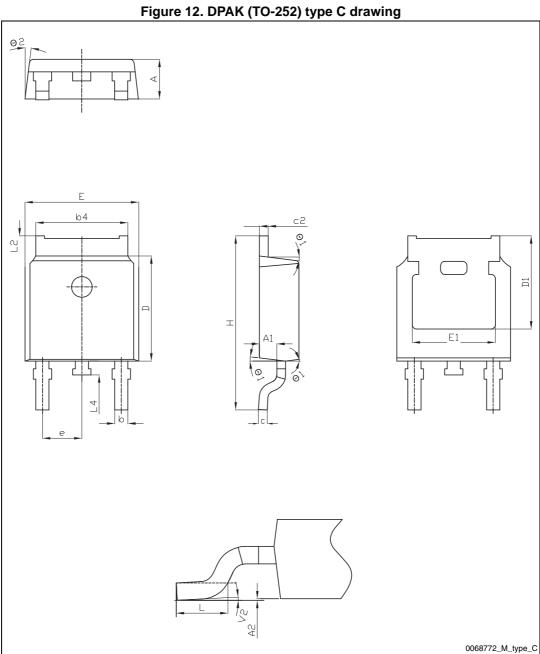
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.

Dim		mm	
Dim. —	Min.	Тур.	Max.
А	2.20	2.30	2.38
A1	0.90	1.01	1.10
A2	0.00		0.10
b	0.72		0.85
b4	5.13	5.33	5.46
с	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.25		
E	6.50	6.60	6.70
E1	4.70		
е	2.186	2.286	2.386
Н	9.80	10.10	10.40
L	1.40	1.50	1.70
L2	0.90		1.25
L4	0.60	0.80	1.00
Θ1	5°	7°	9°
Θ2	5°	7°	9°
V2	0°		8°

Table 5. DPAK (TO-252) type C mechanical data







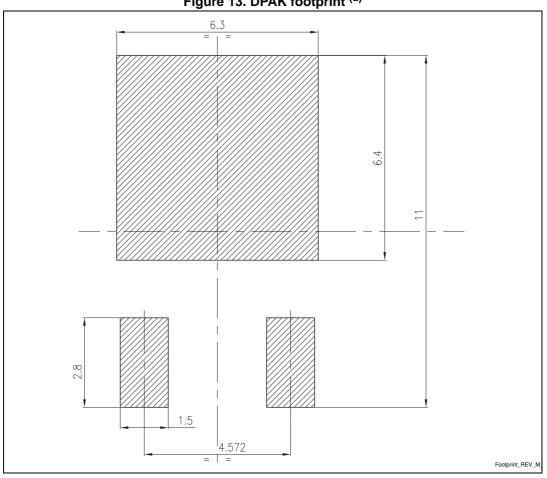


Figure 13. DPAK footprint ^(a)

a. All dimensions are in millimeters



5 Packing mechanical data

	Table 6. DPAR (10-252) tape and feel mechanical data				
Таре			Reel		
Dim.	n	ım	Dim.	mm	
Dim.	Min.	Max.	Dini.	Min.	Max.
A0	6.8	7	А		330
B0	10.4	10.6	В	1.5	
B1		12.1	С	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
Е	1.65	1.85	N	50	
F	7.4	7.6	Т		22.4
K0	2.55	2.75			
P0	3.9	4.1		Base qty.	2500
P1	7.9	8.1		Bulk qty.	2500
P2	1.9	2.1			
R	40				
Т	0.25	0.35			
W	15.7	16.3			

Table 6. DPAK (TO-252) tape and reel mechanical data



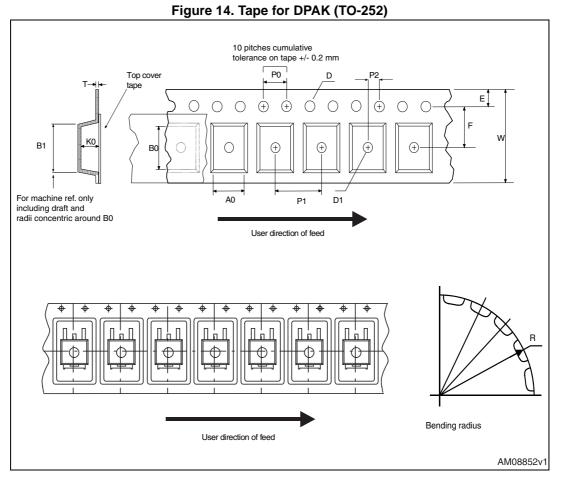
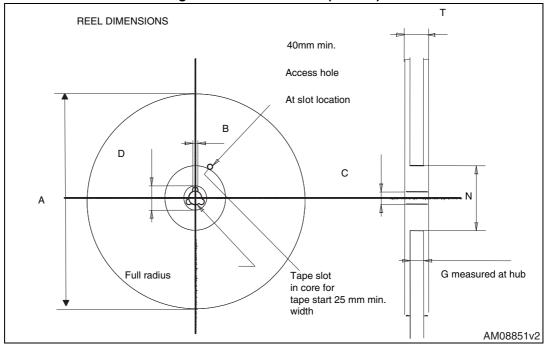


Figure 15. Reel for DPAK (TO-252)



DocID025553 Rev 1



6 Revision history

Table 7. Doo	cument revis	ion history
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Date	Revision	Changes
19-Nov-2013	1	Initial release.



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